



PATENT
Attorney Docket No.: SAM-0298

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#13/Pre.

Applicant(s): Jae-Hak Kim, et al.

Examiner: Rao, S.

Serial No.: 09/994,508

Group Art Unit: 2814

Filing Date: November 27, 2001

Title: METHOD OF FABRICATING SEMICONDUCTOR DEVICES HAVING LOW
DIELECTRIC INTERLAYER INSULATION LAYER

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marsha
6/4/03

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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May 27, 2003
Date

Lisa Sanders
Lisa Sanders

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

This is in response to the final Office Action mailed on September 26, 2002, and the Advisory Action received by the applicants via facsimile on March 26, 2003, in response to the applicants' Amendment After Final Rejection mailed on December 6, 2002. As indicated in the Advisory Action, the Amendment After Final Rejection has been entered upon the filing of applicants' Notice of Appeal on March 26, 2003. With this filing of the attached Request for Continued Examination (RCE), the Appeal is withdrawn.

Please amend the application as follows:

In the Claims

1. (Three Times Amended) A method of fabricating a semiconductor device having a low dielectric interlayer insulation layer, the method comprising:
completely forming a silicon oxycarbide layer as the low dielectric interlayer